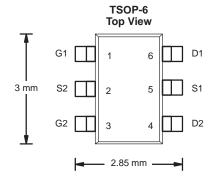


Dual N-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	$R_{DS(on)}$ (Ω)	I _D (A) ^a	Q _g (Typ.)			
20	0.022 at $V_{GS} = 4.5 \text{ V}$	4.8	1.8 nC			
	0.029 at V _{GS} = 2.5 V	3.3	1.0110			



FEATURES

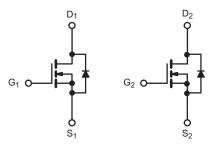
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC



ROHS COMPLIANT HALOGEN FREE

APPLICATIONS

- Load Switch for Portable Applications
- DC/DC Converters



N-Channel MOSFET

N-Channel MOSFET

Parameter	Symbol	Limit	Unit		
Drain-Source Voltage	V _{DS}	20 ± 12			
Gate-Source Voltage	V _{GS}				
	T _C = 25 °C		4.8		
Continuous Drain Current (T _{.I} = 150 °C)	T _C = 70 °C		3		
Continuous Diam Current (1) = 130 C)	T _A = 25 °C	- I _D -	3.4 ^{b, c}		
	T _A = 70 °C	1 -	2.7 ^{b, c}	A	
Pulsed Drain Current		I _{DM}	15		
	T _C = 25 °C		1.17		
Continuous Source-Drain Diode Current	T _A = 25 °C	I _S	0.95 ^{b, c}		
	T _C = 25 °C		1.4		
Maximum Power Dissipation	T _C = 70 °C	P _D	0.9	W	
Maximum Fower Dissipation	T _A = 25 °C	1 'D	1.14 ^{b, c}	VV	
	T _A = 70 °C		0.73 ^{b, c}		
Operating Junction and Storage Temperature	T _J , T _{stg}	- 55 to 150	°C		
Soldering Recommendations (Peak Tempera		260			

THERMAL RESISTANCE RATINGS								
Parameter	Symbol	Typical	Maximum	Unit				
Maximum Junction-to-Ambient ^{b, d}	t ≤ 5 s	R _{thJA}	93	110	°C/W			
Maximum Junction-to-Foot	Steady State	R_{thJF}	75	90	C/ VV			

Notes:

- a. $T_C = 25$ °C.
- b. Surface Mounted on 1" x 1" FR4 board.
- c. t = 5 s
- d. Maximum under steady state conditions is 150 $^{\circ}\text{C/W}.$

Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static				•		
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V, I}_{D} = 250 \mu\text{A}$	20			V
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	$\Delta V_{DS}/T_{J}$ $I_{D} = 250 \mu A$		29		mV/°C
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	1D = 230 μΑ		- 4		mv/·C
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	0.5		1.5	V
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			± 100	nA
Zara Oata Valta va Basis Oursest	I _{DSS}	V _{DS} = 20 V, V _{GS} = 0 V			1	μA
Zero Gate Voltage Drain Current		V _{DS} = 20 V, V _{GS} = 0 V, T _J = 55 °C			10	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	10			Α
	В	$V_{GS} = 4.5 \text{ V}, I_D = 3.4 \text{ A}$		0.022	0.025	Ω
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 2.5 \text{ V}, I_D = 3.0 \text{ A}$		0.029	0.032	
Forward Transconductance ^a	g _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 3.4 \text{ A}$		10		S
Dynamic ^b						
Input Capacitance	C _{iss}			235		pF
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		45		
Reverse Transfer Capacitance	C _{rss}			16		
T. 10 . 0	Qg	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 3.4 \text{ A}$		3.7	6	nC
Total Gate Charge				1.8	3	
Gate-Source Charge	Q _{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 3.4 \text{ A}$		0.74		
Gate-Drain Charge	Q_{gd}			0.42		
Gate Resistance	R_g	f = 1 MHz	1	5	10	Ω
Turn-On Delay Time	t _{d(on)}			10	20	
Rise Time	t _r	V_{DD} = 15 V, R_L = 5.6 Ω		15	30	
Turn-Off Delay Time	t _{d(off)}	$I_D\cong 2.7$ A, V_{GEN} = 4.5 V, R_g = 1 Ω		10	20	
Fall Time	t _f			10	20	
Turn-On Delay Time	t _{d(on)}			5	10	ns -
Rise Time	t _r	V_{DD} = 15 V, R_L = 5.6 Ω		15	30	
Turn-Off Delay Time	t _{d(off)}	$I_D\cong 2.7$ A, V_{GEN} = 4.5 V, R_g = 1 Ω		10	20	
Fall Time	t _f			10	20	
Drain-Source Body Diode Characteristic	s					
Continuous Source-Drain Diode Current	I _S	$T_C = 25 ^{\circ}C$			1.17	А
Pulse Diode Forward Current	I _{SM}				15	
Body Diode Voltage	V_{SD}	$I_S = 2.7 \text{ A}, V_{GS} = 0 \text{ V}$		0.85	1.2	V
Body Diode Reverse Recovery Time	t _{rr}			10	20	ns
Body Diode Reverse Recovery Charge	very Charge Q_{rr} $I_F = 2.7 \text{ A, dl/dt} = 100 \text{ A/µs, T}_J = 25 °C$			4	10	nC
Reverse Recovery Fall Time	t _a	t _a		6		ne
Reverse Recovery Rise Time	t _b			4		ns

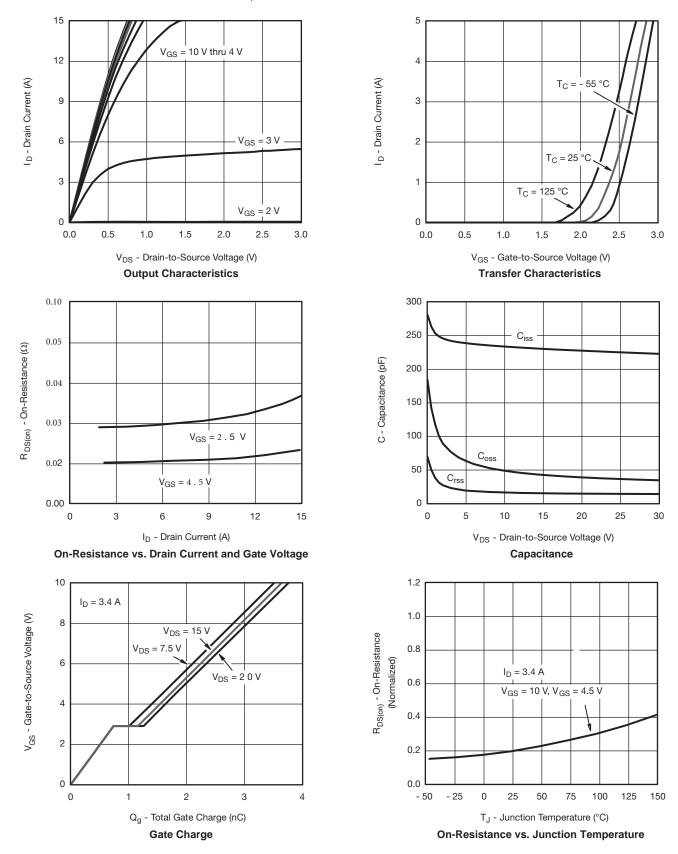
Notes:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%$

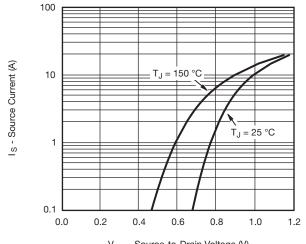
b. Guaranteed by design, not subject to production testing.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



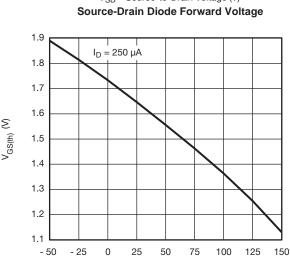


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

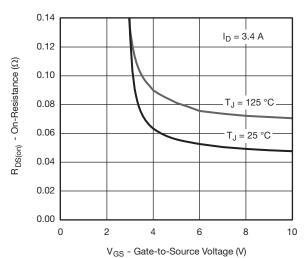


Din-Tek

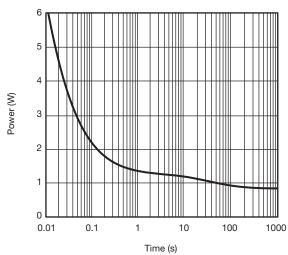
V_{SD} - Source-to-Drain Voltage (V)



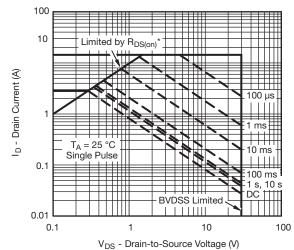
T_J - Temperature (°C) **Threshold Voltage**



On-Resistance vs. Gate-to-Source Voltage



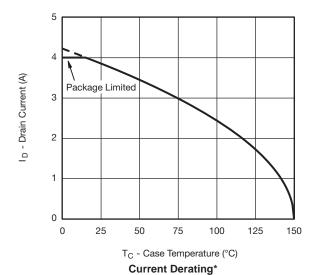
Single Pulse Power (Junction-to-Ambient)

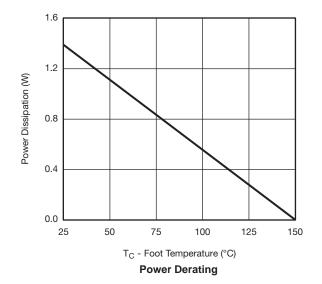


 $^*\,V_{GS}>$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



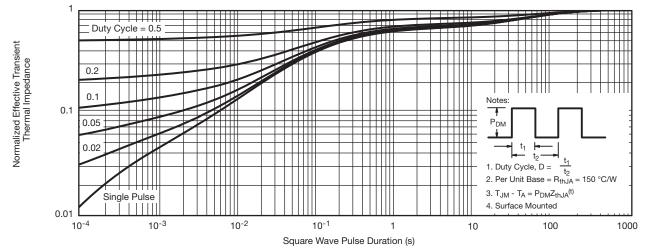


^{*} The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

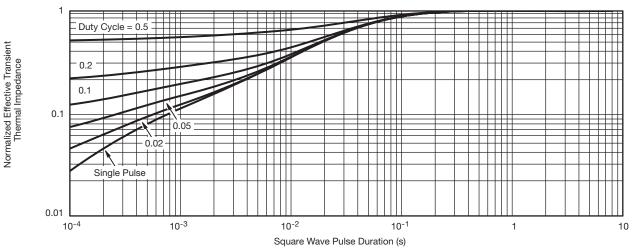


TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

Din-Tek SEMICONDUCTOR



Normalized Thermal Transient Impedance, Junction-to-Ambient

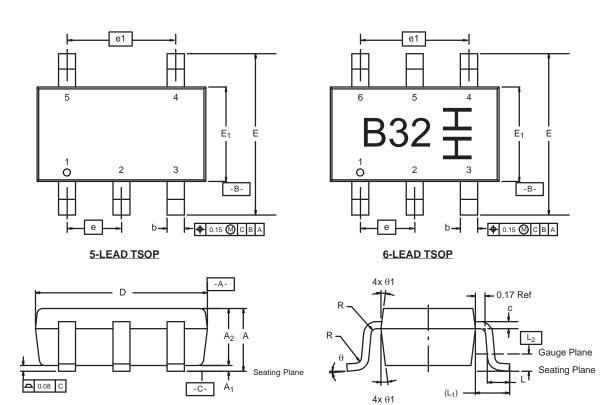


Normalized Thermal Transient Impedance, Junction-to-Foot



TSOP: 5/6-LEAD

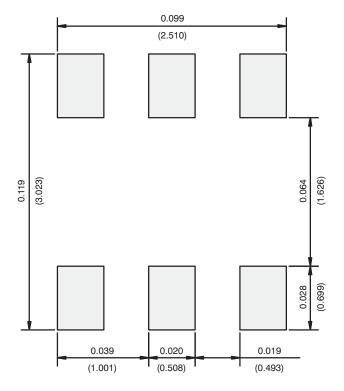
JEDEC Part Number: MO-193C



	MILLIMETERS			INCHES			
Dim	Min	Nom	Max	Min	Nom	Max	
Α	0.91	-	1.10	0.036	-	0.043	
A ₁	0.01	-	0.10	0.0004	-	0.004	
A ₂	0.90	-	1.00	0.035	0.038	0.039	
b	0.30	0.32	0.45	0.012	0.013	0.018	
С	0.10	0.15	0.20	0.004	0.006	0.008	
D	2.95	3.05	3.10	0.116	0.120	0.122	
Е	2.70	2.85	2.98	0.106	0.112	0.117	
E ₁	1.55	1.65	1.70	0.061	0.065	0.067	
е	0.95 BSC			0.0374 BSC			
e ₁	1.80	1.90	2.00	0.071	0.075	0.079	
L	0.32	-	0.50	0.012	-	0.020	
L ₁		0.60 Ref		0.024 Ref			
L ₂	0.25 BSC			0.010 BSC			
R	0.10	-	-	0.004	-	-	
θ	0°	4°	8°	0°	4°	8°	
θ1	7° Nom			7° Nom			
ECN: C-06593-Rev. I, 18-Dec-06 DWG: 5540							



RECOMMENDED MINIMUM PADS FOR TSOP-6



Recommended Minimum Pads Dimensions in Inches/(mm)



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